

TENTATIVE

Features and Applications

- Low ON-state resistance.
- Very high - speed switching.
- 4V drive.

Absolute Maximum Ratings / Ta=25°C

			unit
Drain to Source Voltage	VDSS	30	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID	45	A
Drain Current (Pulse)	IDP	80	A
Allowable power Dissipation	PD	1.65	W
		40	W
		150	°C
Channel Temperature	Tch		
Storage Temperature	Tstg	-55 to +150	°C

Tc=25°C

Electrical Characteristics / Ta=25°C

			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA , VGS=0	30			V
Zero Gate Voltage Drain Current	IDSS	VDS=30V , VGS=0			1	μA
Gate to Source Leakage Current	IGSS	VGS=±16V , VDS=0			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V , ID=1mA	1.0		2.4	V
Forward Transfer Admittance	yfs	VDS=10V , ID=20A	19	27		S
Static Drain to Source on State Resistance	RDS(on)	ID=20A , VGS=10V		11	15	mΩ
	RDS(on)	ID=10A , VGS=4.5V		15	21	mΩ
Input Capacitance	Ciss	VDS=10V , f=1MHz		1400		pF
Output Capacitance	Coss	VDS=10V , f=1MHz		420		pF
Reverse Transfer Capacitance	Crss	VDS=10V , f=1MHz		210		pF
Turn-ON Delay Time	td(on)			14		ns
Rise Time	tr			530		ns
Turn-oFF Delay Time	td(off)			100		ns
Fall Time	tf			150		ns
Total Gate Charge	Qg			28		nC
Gate Source Charge	Qgs			4.6		nC
Gate Drain Charge	Qgd			5		nC
Diode Forward Voltage	VSD	IS=45A , VGS= 0	1.0	1.2		V

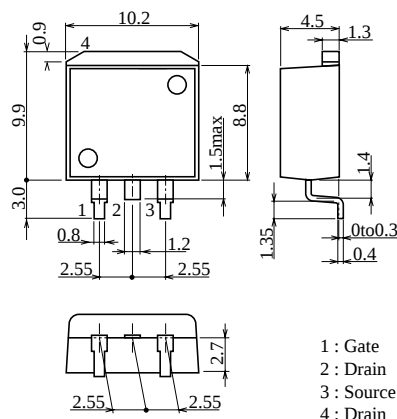
See specified Test Circuit

VDS=10V, VGS=10V, ID=20A

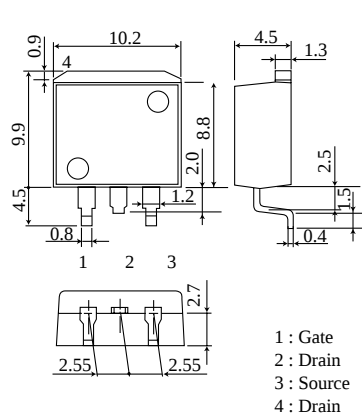
Marking : K3352

Package Dimensions

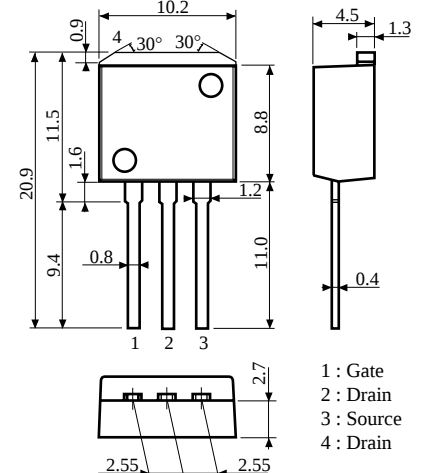
SMP-FD (unit : mm)



SMP-FA (unit : mm)



SMP(unit:mm)



Specifications and information herein are subject to change without notice.

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990915TM2fXHD

Switching Time Test Circuit

